BT139-600E



4Q Triac

Rev. 05 — 24 March 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.2 Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

1.3 Applications

General purpose motor control

General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|---|--|-----|-----|-----|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 600 | V |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see Figure 4; see Figure 5 | - | - | 155 | Α |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u> | - | - | 16 | Α |



Table 1. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------|----------------------|---|-----|------|-----|------|
| Static chara | | | | -71- | | |
| I _{GT} gate trigger of | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ Composition}}$ | - | 2.5 | 10 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G -;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ Composition}}$ | 4 | 10 | mA | |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$ | - | 5 | 10 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G+;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$ | - | 11 | 25 | mA |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|--------------------|----------------|
| 1 | T1 | main terminal 1 | | . . |
| 2 | T2 | main terminal 2 | mb | T2 T1 |
| 3 | G | gate | | `G sym051 |
| mb | T2 | mounting base; main terminal 2 | | |

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|----------|--|---------|
| | Name | Description | Version |
| BT139-600E | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |
| BT139-600E/DG | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|---|-----|-----|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 600 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; T _{mb} ≤ 99 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u> | - | 16 | Α |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u> | - | 155 | Α |
| | | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$ | - | 170 | Α |
| l ² t | I ² t for fusing | t _p = 10 ms; sine-wave pulse | - | 120 | A ² s |
| dI _T /dt | rate of rise of on-state current | I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G+ | - | 50 | A/µs |
| | | I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G- | - | 50 | A/µs |
| | | I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G- | - | 50 | A/µs |
| | | $I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s};$ T2- G+ | - | 10 | A/µs |
| I _{GM} | peak gate current | | - | 2 | Α |
| V_{GM} | peak gate voltage | | - | 5 | V |
| P_GM | peak gate power | | - | 5 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 125 | °C |

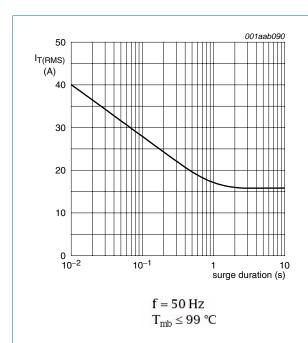


Fig 1. RMS on-state current as a function of surge duration; maximum values

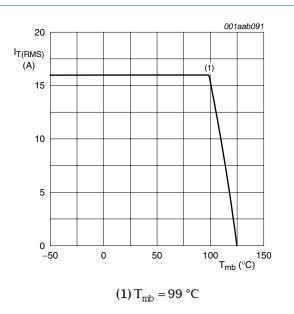


Fig 2. RMS on-state current as a function of mounting base temperature; maximum values

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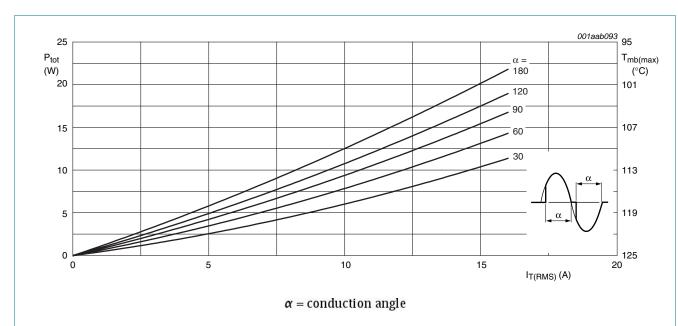
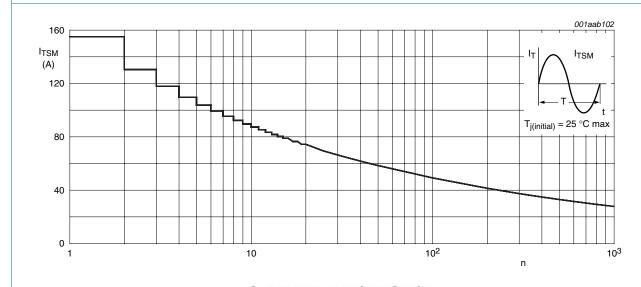
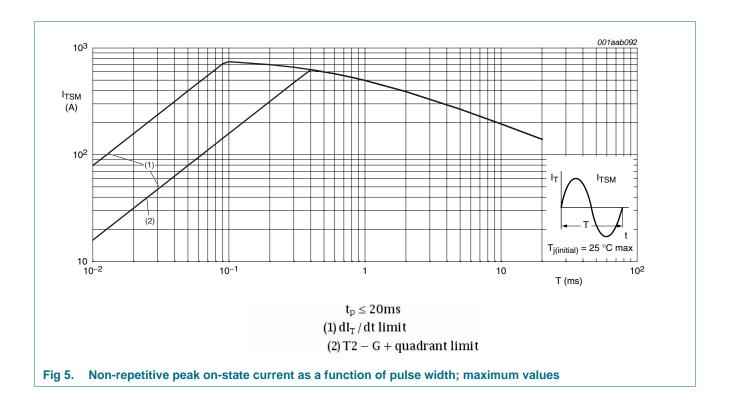


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values.



f = 50 Hz; n = number of cycles

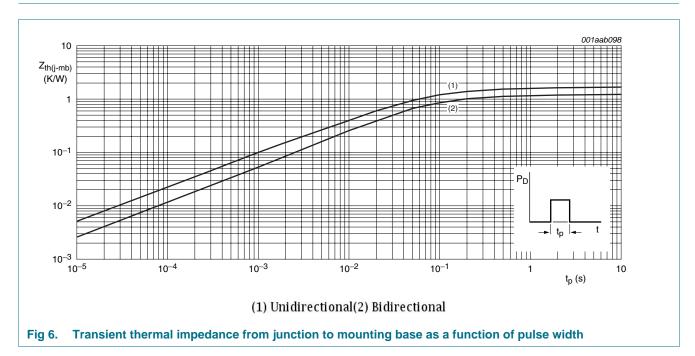
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|--------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to | half cycle; see Figure 6 | - | - | 1.7 | K/W |
| | mounting base | full cycle; see Figure 6 | - | - | 1.2 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |



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6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|-----------------------------------|--|------|-----|-----|------|
| Static cha | racteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+G+; T_j = 25 ^{\circ}\text{C};$ see Figure 7 | - | 2.5 | 10 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}C;$ see Figure 7 | - | 4 | 10 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-}; T_j = 25 ^{\circ}\text{C};$ see Figure 7 | - | 5 | 10 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; T_j = 25 ^{\circ}\text{C};$ see Figure 7 | - | 11 | 25 | mA |
| I _L latchi | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$ | - | 3.2 | 30 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8 | - | 16 | 40 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8 | - | 4 | 30 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+; T_j = 25 ^{\circ}\text{C};$ see Figure 8 | - | 5.5 | 40 | mA |
| I _H | holding current | $V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{My second of the second o$ | - | 4 | 45 | mΑ |
| V _T | on-state voltage | I _T = 20 A; T _j = 25 °C; see <u>Figure 10</u> | - | 1.2 | 1.6 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11 | - | 0.7 | 1.5 | V |
| | | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11 | 0.25 | 0.4 | - | V |
| I _D | off-state current | $V_D = 600 \text{ V}; T_j = 125 ^{\circ}\text{C}$ | - | 0.1 | 0.5 | mΑ |
| Dynamic o | haracteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 402 V; T_j = 125 °C; exponential waveform; gate open circuit | - | 50 | - | V/µs |
| t _{gt} | gate-controlled turn-on time | $I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A/}\mu\text{s}$ | - | 2 | - | μs |

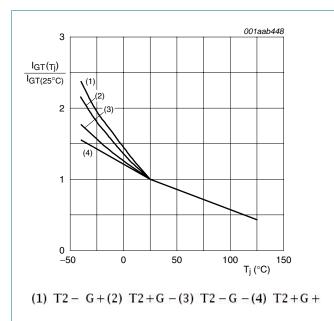


Fig 7. Normalized gate trigger current as a function of junction temperature

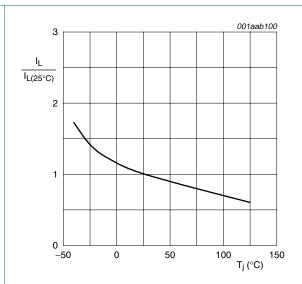


Fig 8. Normalized latching current as a function of junction temperature

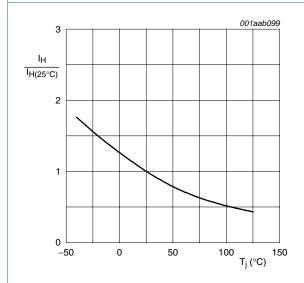
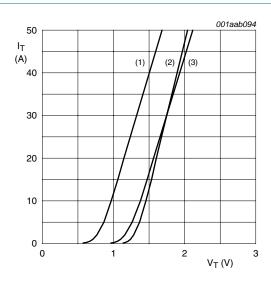


Fig 9. Normalized holding current as a function of junction temperature



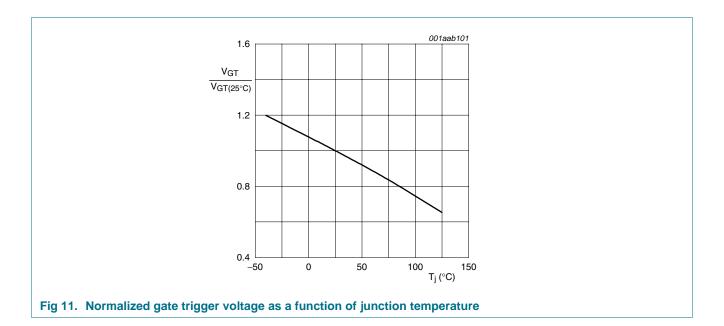
 $\begin{aligned} V_o &= 1.195 \, V \\ R_s &= 0.018 \, \Omega \end{aligned}$

(1) $T_j = 125$ °C; typical values

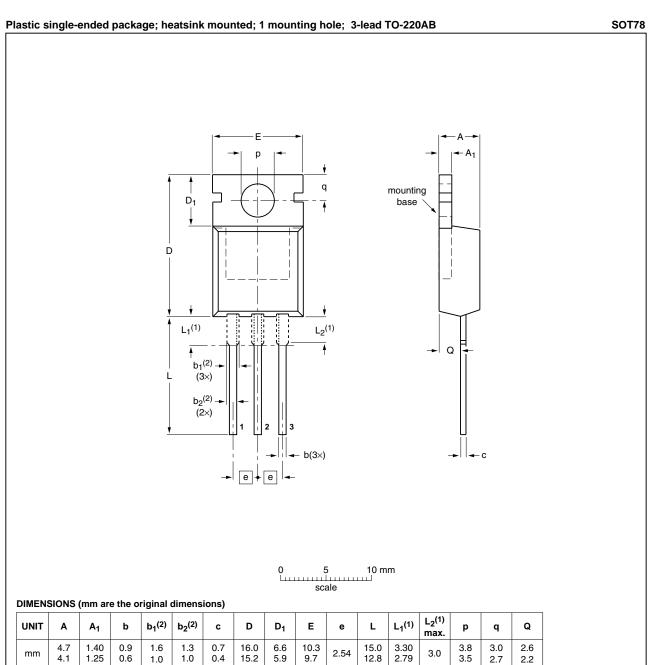
(2) $T_j = 25$ °C; maximum values

(3) $T_j = 125$ °C; maximum values

Fig 10. On-state current as a function of on-state voltage



Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|---------|-----|-----------------|-------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE |
| SOT78 | | 3-lead TO-220AB | SC-46 | | 08-04-23 08-06-13 |

Fig 12. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|-----------------------------------|--------------------|---------------|-----------------|
| BT139-600E v.5 | 20110324 | Product data sheet | - | BT139-600E v.4 |
| Modifications: | Various chang | es to content. | | |
| BT139-600E v.4 | 20110224 | Product data sheet | - | BT139_SER_E v.3 |

9. Legal information

9.1 Data sheet status

| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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